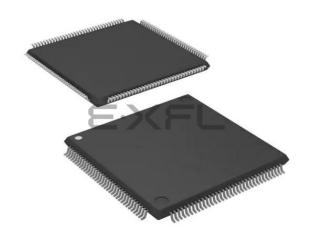
Intel - EPM570T144A5N Datasheet





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Understanding <u>Embedded - CPLDs (Complex</u> <u>Programmable Logic Devices)</u>

Embedded - CPLDs, or Complex Programmable Logic Devices, are highly versatile digital logic devices used in electronic systems. These programmable components are designed to perform complex logical operations and can be customized for specific applications. Unlike fixedfunction ICs, CPLDs offer the flexibility to reprogram their configuration, making them an ideal choice for various embedded systems. They consist of a set of logic gates and programmable interconnects, allowing designers to implement complex logic circuits without needing custom hardware.

Applications of Embedded - CPLDs

Details

Product Status	Active
Programmable Type	In System Programmable
Delay Time tpd(1) Max	5.4 ns
Voltage Supply - Internal	2.5V, 3.3V
Number of Logic Elements/Blocks	570
Number of Macrocells	440
Number of Gates	-
Number of I/O	116
Operating Temperature	-40°C ~ 125°C (TJ)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-TQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/intel/epm570t144a5n

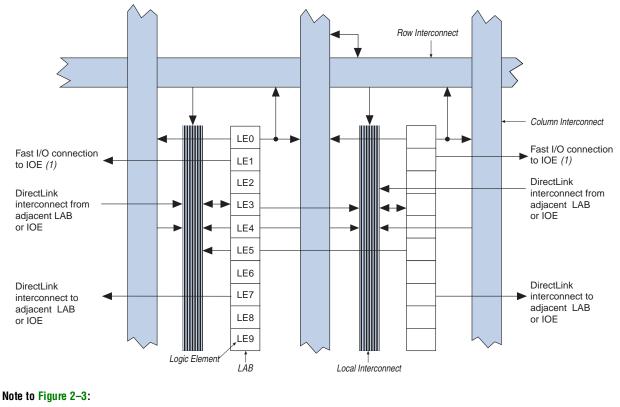
Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

Logic Array Blocks

Each LAB consists of 10 LEs, LE carry chains, LAB control signals, a local interconnect, a look-up table (LUT) chain, and register chain connection lines. There are 26 possible unique inputs into an LAB, with an additional 10 local feedback input lines fed by LE outputs in the same LAB. The local interconnect transfers signals between LEs in the same LAB. LUT chain connections transfer the output of one LE's LUT to the adjacent LE for fast sequential LUT connections within the same LAB. Register chain connections transfer the output of one LE's register chain connections transfer the output of one LE's register chain an LAB or adjacent LAB. The Quartus® II software places associated logic within an LAB or adjacent LABs, allowing the use of local, LUT chain, and register chain connections for performance and area efficiency. Figure 2–3 shows the MAX II LAB.

Figure 2–3. MAX II LAB Structure

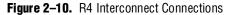


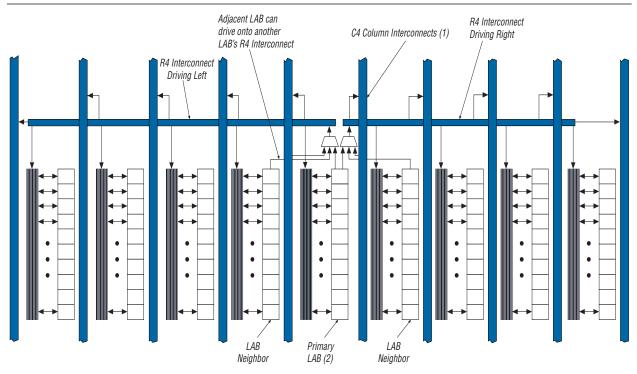
(1) Only from LABs adjacent to IOEs.

LAB Interconnects

The LAB local interconnect can drive LEs within the same LAB. The LAB local interconnect is driven by column and row interconnects and LE outputs within the same LAB. Neighboring LABs, from the left and right, can also drive an LAB's local interconnect through the DirectLink connection. The DirectLink connection feature minimizes the use of row and column interconnects, providing higher performance and flexibility. Each LE can drive 30 other LEs through fast local and DirectLink interconnects. Figure 2–4 shows the DirectLink connection.

The R4 interconnects span four LABs and are used for fast row connections in a four-LAB region. Every LAB has its own set of R4 interconnects to drive either left or right. Figure 2–10 shows R4 interconnect connections from an LAB. R4 interconnects can drive and be driven by row IOEs. For LAB interfacing, a primary LAB or horizontal LAB neighbor can drive a given R4 interconnect. For R4 interconnects that drive to the right, the primary LAB and right neighbor can drive on to the interconnect. For R4 interconnects that drive to the left, the primary LAB and its left neighbor can drive on to the interconnect. R4 interconnects can drive other R4 interconnects to extend the range of LABs they can drive. R4 interconnects can also drive C4 interconnects for connections from one row to another.





Notes to Figure 2–10:

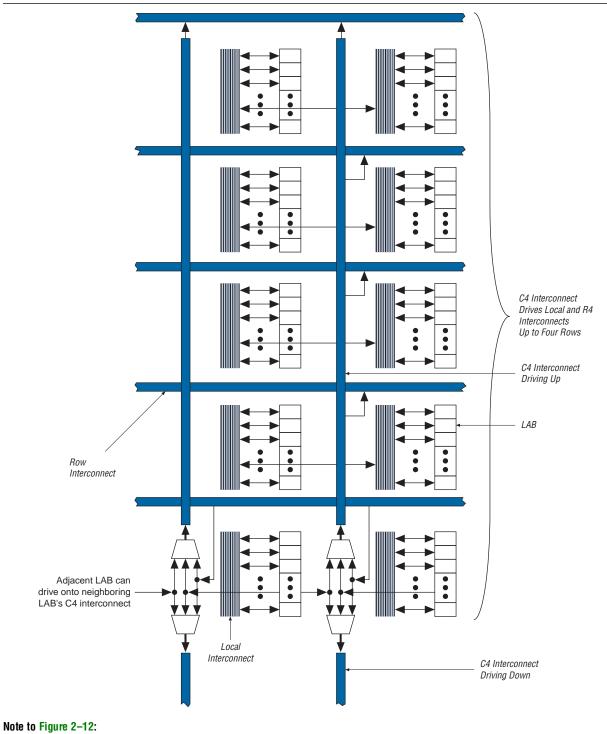
- (1) C4 interconnects can drive R4 interconnects.
- (2) This pattern is repeated for every LAB in the LAB row.

The column interconnect operates similarly to the row interconnect. Each column of LABs is served by a dedicated column interconnect, which vertically routes signals to and from LABs and row and column IOEs. These column resources include:

- LUT chain interconnects within an LAB
- Register chain interconnects within an LAB
- C4 interconnects traversing a distance of four LABs in an up and down direction

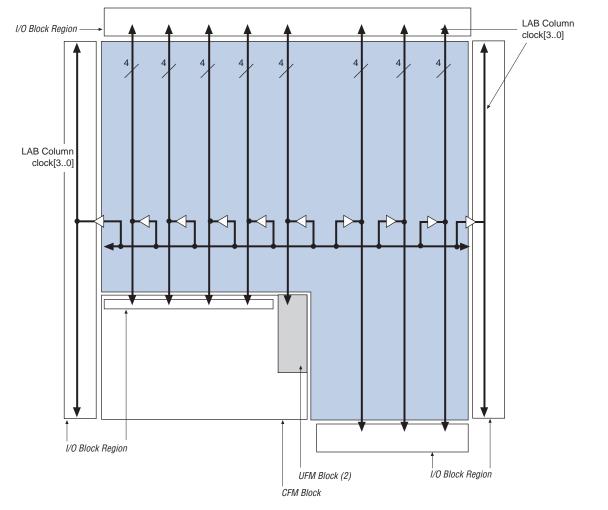
MAX II devices include an enhanced interconnect structure within LABs for routing LE output to LE input connections faster using LUT chain connections and register chain connections. The LUT chain connection allows the combinational output of an LE to directly drive the fast input of the LE right below it, bypassing the local interconnect. These resources can be used as a high-speed connection for wide fan-in

Figure 2–12. C4 Interconnect Connections (Note 1)



(1) Each C4 interconnect can drive either up or down four rows.

Figure 2–14. Global Clock Network (Note 1)



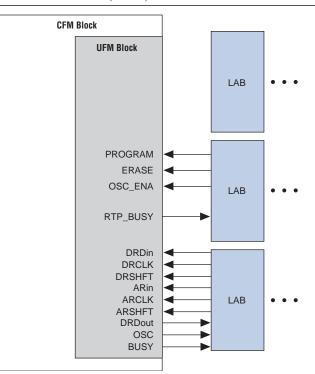
Notes to Figure 2–14:

- (1) LAB column clocks in I/O block regions provide high fan-out output enable signals.
- (2) LAB column clocks drive to the UFM block.

User Flash Memory Block

MAX II devices feature a single UFM block, which can be used like a serial EEPROM for storing non-volatile information up to 8,192 bits. The UFM block connects to the logic array through the MultiTrack interconnect, allowing any LE to interface to the UFM block. Figure 2–15 shows the UFM block and interface signals. The logic array is used to create customer interface or protocol logic to interface the UFM block data outside of the device. The UFM block offers the following features:

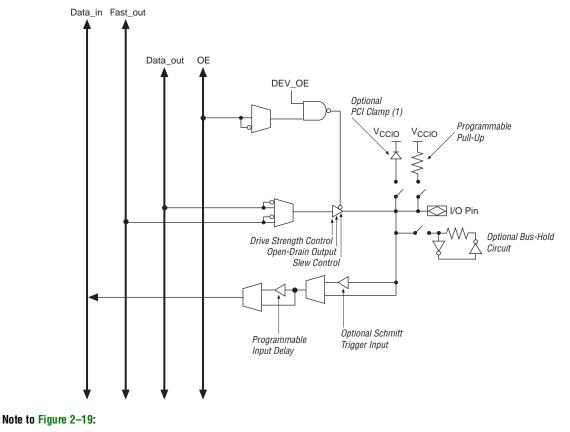
- Non-volatile storage up to 16-bit wide and 8,192 total bits
- Two sectors for partitioned sector erase
- Built-in internal oscillator that optionally drives logic array
- Program, erase, and busy signals



Note to Figure 2–16:

(1) The UFM block inputs and outputs can drive to/from all types of interconnects, not only DirectLink interconnects from adjacent row LABs.





(1) Available in EPM1270 and EPM2210 devices only.

I/O Blocks

The IOEs are located in I/O blocks around the periphery of the MAX II device. There are up to seven IOEs per row I/O block (5 maximum in the EPM240 device) and up to four IOEs per column I/O block. Each column or row I/O block interfaces with its adjacent LAB and MultiTrack interconnect to distribute signals throughout the device. The row I/O blocks drive row, column, or DirectLink interconnects. The column I/O blocks drive column interconnects.

Bus Hold

Each MAX II device I/O pin provides an optional bus-hold feature. The bus-hold circuitry can hold the signal on an I/O pin at its last-driven state. Since the bus-hold feature holds the last-driven state of the pin until the next input signal is present, an external pull-up or pull-down resistor is not necessary to hold a signal level when the bus is tri-stated.

The bus-hold circuitry also pulls undriven pins away from the input threshold voltage where noise can cause unintended high-frequency switching. The designer can select this feature individually for each I/O pin. The bus-hold output will drive no higher than $V_{\rm CCIO}$ to prevent overdriving signals. If the bus-hold feature is enabled, the device cannot use the programmable pull-up option.

The bus-hold circuitry uses a resistor to pull the signal level to the last driven state. The *DC and Switching Characteristics* chapter in the *MAX II Device Handbook* gives the specific sustaining current for each V_{CCIO} voltage level driven through this resistor and overdrive current used to identify the next-driven input level.

The bus-hold circuitry is only active after the device has fully initialized. The bus-hold circuit captures the value on the pin present at the moment user mode is entered.

Programmable Pull-Up Resistor

Each MAX II device I/O pin provides an optional programmable pull-up resistor during user mode. If the designer enables this feature for an I/O pin, the pull-up resistor holds the output to the V_{CCIO} level of the output pin's bank.



The programmable pull-up resistor feature should not be used at the same time as the bus-hold feature on a given I/O pin.

Programmable Input Delay

The MAX II IOE includes a programmable input delay that is activated to ensure zero hold times. A path where a pin directly drives a register, with minimal routing between the two, may require the delay to ensure zero hold time. However, a path where a pin drives a register through long routing or through combinational logic may not require the delay to achieve a zero hold time. The Quartus II software uses this delay to ensure zero hold times when needed.

MultiVolt I/O Interface

The MAX II architecture supports the MultiVolt I/O interface feature, which allows MAX II devices in all packages to interface with systems of different supply voltages. The devices have one set of VCC pins for internal operation (V_{CCINT}), and up to four sets for input buffers and I/O output driver buffers (V_{CCIO}), depending on the number of I/O banks available in the devices where each set of VCC pins powers one I/O bank. The EPM240 and EPM570 devices have two I/O banks respectively while the EPM1270 and EPM2210 devices have four I/O banks respectively.

Device	Version (4 Bits)	Part Number	Manufacturer Identity (11 Bits)	LSB (1 Bit) <i>(2)</i>	HEX IDCODE
EPM240Z	0000	0010 0000 1010 0101	000 0110 1110	1	0x020A50DD
EPM570Z	0000	0010 0000 1010 0110	000 0110 1110	1	0x020A60DD

Table 3-3. 32-Bit MAX II Device IDCODE (Part 2 of 2)

Notes to Table 3-2:

(1) The most significant bit (MSB) is on the left.

(2) The IDCODE's least significant bit (LSB) is always 1.

• For more information about JTAG BST, refer to the *IEEE 1149.1 (JTAG) Boundary-Scan Testing for MAX II Devices* chapter in the *MAX II Device Handbook*.

JTAG Block

The MAX II JTAG block feature allows you to access the JTAG TAP and state signals when either the USER0 or USER1 instruction is issued to the JTAG TAP. The USER0 and USER1 instructions bring the JTAG boundary-scan chain (TDI) through the user logic instead of the MAX II device's boundary-scan cells. Each USER instruction allows for one unique user-defined JTAG chain into the logic array.

Parallel Flash Loader

The JTAG block ability to interface JTAG to non-JTAG devices is ideal for generalpurpose flash memory devices (such as Intel- or Fujitsu-based devices) that require programming during in-circuit test. The flash memory devices can be used for FPGA configuration or be part of system memory. In many cases, the MAX II device is already connected to these devices as the configuration control logic between the FPGA and the flash device. Unlike ISP-capable CPLD devices, bulk flash devices do not have JTAG TAP pins or connections. For small flash devices, it is common to use the serial JTAG scan chain of a connected device to program the non-JTAG flash device. This is slow and inefficient in most cases and impractical for large parallel flash devices. Using the MAX II device's JTAG block as a parallel flash loader, with the Quartus II software, to program and verify flash contents provides a fast and costeffective means of in-circuit programming during test. Figure 3–1 shows MAX II being used as a parallel flash loader.

For JTAG AC characteristics, refer to the DC and Switching Characteristics chapter in the MAX II Device Handbook.

Document Revision History

Table 3–5 shows the revision history for this chapter.

Table 3–5.	Document Revision History

Date and Revision	Changes Made	Summary of Changes
October 2008, version 1.6	 Updated New Document Format. 	_
December 2007, version 1.5	Added warning note after Table 3–1.	—
	Updated Table 3–3 and Table 3–4.	
	 Added "Referenced Documents" section. 	
December 2006, version 1.4	Added document revision history.	_
June 2005, version 1.3	Added text and Table 3-4.	-
June 2005, version 1.3	 Updated text on pages 3-5 to 3-8. 	_
June 2004, version 1.1	Corrected Figure 3-1. Added CFM acronym.	_

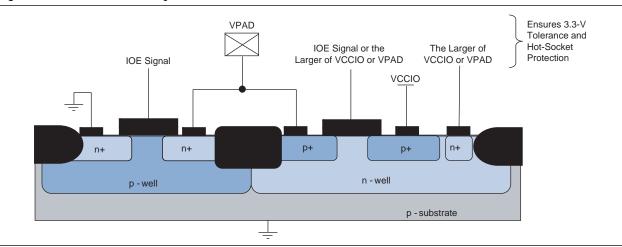
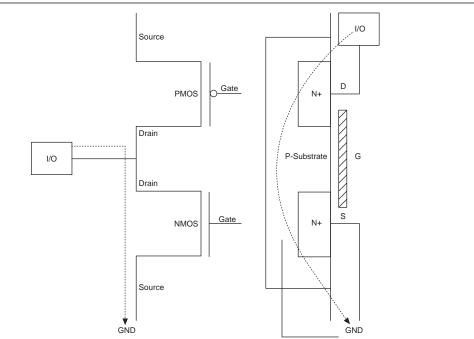


Figure 4–2. Transistor-Level Diagram of MAX II Device I/O Buffers

The CMOS output drivers in the I/O pins intrinsically provide electrostatic discharge (ESD) protection. There are two cases to consider for ESD voltage strikes: positive voltage zap and negative voltage zap.

A positive ESD voltage zap occurs when a positive voltage is present on an I/O pin due to an ESD charge event. This can cause the N+ (Drain)/ P-Substrate junction of the N-channel drain to break down and the N+ (Drain)/P-Substrate/N+ (Source) intrinsic bipolar transistor turn on to discharge ESD current from I/O pin to GND. The dashed line (see Figure 4–3) shows the ESD current discharge path during a positive ESD zap.

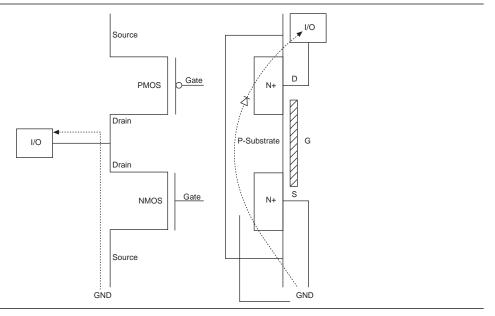
Figure 4-3. ESD Protection During Positive Voltage Zap



When the I/O pin receives a negative ESD zap at the pin that is less than -0.7 V (0.7 V is the voltage drop across a diode), the intrinsic

P-Substrate/N+ drain diode is forward biased. Therefore, the discharge ESD current path is from GND to the I/O pin, as shown in Figure 4–4.





Power-On Reset Circuitry

MAX II devices have POR circuits to monitor V_{CCINT} and V_{CCIO} voltage levels during power-up. The POR circuit monitors these voltages, triggering download from the non-volatile configuration flash memory (CFM) block to the SRAM logic, maintaining tri-state of the I/O pins (with weak pull-up resistors enabled) before and during this process. When the MAX II device enters user mode, the POR circuit releases the I/O pins to user functionality. The POR circuit of the MAX II (except MAX IIZ) device continues to monitor the V_{CCINT} voltage level to detect a brown-out condition. The POR circuit of the MAX IIZ device does not monitor the V_{CCINT} voltage level after the device enters into user mode. More details are provided in the following sub-sections.

5. DC and Switching Characteristics



MII51005-2.5

Introduction

System designers must consider the recommended DC and switching conditions discussed in this chapter to maintain the highest possible performance and reliability of the MAX[®] II devices. This chapter contains the following sections:

- "Operating Conditions" on page 5–1
- "Power Consumption" on page 5–8
- "Timing Model and Specifications" on page 5–8

Operating Conditions

Table 5–1 through Table 5–12 provide information about absolute maximum ratings, recommended operating conditions, DC electrical characteristics, and other specifications for MAX II devices.

Absolute Maximum Ratings

Table 5-1 shows the absolute maximum ratings for the MAX II device family.

Table 5-1.	MAX II Device Absolute	Maximum Ratings	(Note 1), (2)
------------	------------------------	-----------------	---------------

Symbol	Parameter	Conditions	Minimum	Maximum	Unit
V _{CCINT}	Internal supply voltage (3)	With respect to ground	-0.5	4.6	V
V _{CCIO}	I/O supply voltage	—	-0.5	4.6	V
Vi	DC input voltage	—	-0.5	4.6	V
I _{OUT}	DC output current, per pin (4)	—	-25	25	mA
T _{STG}	Storage temperature	No bias	-65	150	°C
T _{AMB}	Ambient temperature	Under bias (5)	-65	135	°C
TJ	Junction temperature	TQFP and BGA packages under bias	_	135	0°

Notes to Table 5-1:

(1) Refer to the Operating Requirements for Altera Devices Data Sheet.

(2) Conditions beyond those listed in Table 5–1 may cause permanent damage to a device. Additionally, device operation at the absolute maximum ratings for extended periods of time may have adverse affects on the device.

(3) Maximum $V_{\mbox{\tiny CCINT}}$ for MAX II devices is 4.6 V. For MAX IIG and MAX IIZ devices, it is 2.4 V.

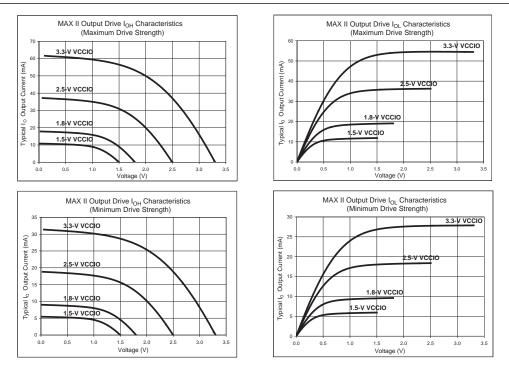
(4) Refer to AN 286: Implementing LED Drivers in MAX & MAX II Devices for more information about the maximum source and sink current for MAX II devices.

(5) Refer to Table 5–2 for information about "under bias" conditions.

Output Drive Characteristics

Figure 5–1 shows the typical drive strength characteristics of MAX II devices.





Note to Figure 5–1:

(1) The DC output current per pin is subject to the absolute maximum rating of Table 5-1.

I/O Standard Specifications

Table 5–5 through Table 5–10 show the MAX II device family I/O standard specifications.

Table 5–5.	3.3-V LVTTL	Specifications
------------	-------------	----------------

Symbol	Parameter	Parameter Conditions Minin		Maximum	Unit
V _{CCIO}	I/O supply voltage	—	3.0	3.6	V
V _{IH}	High-level input voltage	—	1.7	4.0	V
VIL	Low-level input voltage	—	-0.5	0.8	V
V _{OH}	High-level output voltage	IOH = -4 mA (1)	2.4		V
V _{OL}	Low-level output voltage	IOL = 4 mA (1)		0.45	V

Table 5–6. 3.3-V LVCMOS Specifications (Part 1 of 2)

Symbol	Parameter	Parameter Conditions		Maximum	Unit
V _{CCIO}	I/O supply voltage	—	3.0	3.6	V
V _{IH}	High-level input voltage		1.7	4.0	V
VIL	Low-level input voltage		-0.5	0.8	V

Device	Preliminary	Final
EPM1270	—	\checkmark
EPM2210	_	\checkmark

Table 5-13.	MAX II Device	Timing Model Status	(Part 2 of 2)
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Note to Table 5-13:

(1) The MAX IIZ device timing models are only available in the Quartus II software version 8.0 and later.

Performance

Table 5–14 shows the MAX II device performance for some common designs. All performance values were obtained with the Quartus II software compilation of megafunctions. Performance values for –3, –4, and –5 speed grades are based on an EPM1270 device target, while –6, –7, and –8 speed grades are based on an EPM570Z device target.

Table 5–14. MAX II Device Performance

					Performance						
		Reso	ources	Used	MA	X II / MAX	(IIG		MAX IIZ		
Resource Used	Design Size and Function	Mode	LEs	UFM Blocks	–3 Speed Grade	–4 Speed Grade	–5 Speed Grade	–6 Speed Grade	–7 Speed Grade	–8 Speed Grade	Unit
LE	16-bit counter (1)	—	16	0	304.0	247.5	201.1	184.1	123.5	118.3	MHz
	64-bit counter (1)	—	64	0	201.5	154.8	125.8	83.2	83.2	80.5	MHz
	16-to-1 multiplexer	—	11	0	6.0	8.0	9.3	17.4	17.3	20.4	ns
	32-to-1 multiplexer	—	24	0	7.1	9.0	11.4	12.5	22.8	25.3	ns
	16-bit XOR function	—	5	0	5.1	6.6	8.2	9.0	15.0	16.1	ns
	16-bit decoder with single address line	—	5	0	5.2	6.6	8.2	9.2	15.0	16.1	ns
UFM	512 × 16	None	3	1	10.0	10.0	10.0	10.0	10.0	10.0	MHz
	512 × 16	SPI (2)	37	1	8.0	8.0	8.0	9.7	9.7	9.7	MHz
	512 × 8	Parallel <i>(3)</i>	73	1	(4)	(4)	(4)	(4)	(4)	(4)	MHz
	512 × 16	I²C <i>(3)</i>	142	1	100 <i>(5)</i>	100 <i>(5)</i>	100 <i>(5)</i>	100 <i>(5)</i>	100 <i>(5)</i>	100 <i>(5)</i>	kHz

Notes to Table 5-14:

(1) This design is a binary loadable up counter.

(2) This design is configured for read-only operation in Extended mode. Read and write ability increases the number of LEs used.

(3) This design is configured for read-only operation. Read and write ability increases the number of LEs used.

(4) This design is asynchronous.

(5) The I²C megafunction is verified in hardware up to 100-kHz serial clock line (SCL) rate.

				N	IAX II	/ MAX II	G				MA	X IIZ			
				Speed rade		Speed 'ade		Speed ade		speed ade		Speed rade		Speed rade	
Symbol	Parameter	Condition	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
f _{cnt}	Maximum global clock frequency for 16-bit counter			304.0 (1)		247.5		201.1		184.1		123.5		118.3	MHz

 Table 5–24.
 EPM570 Global Clock External I/O Timing Parameters
 (Part 2 of 2)

Note to Table 5-24:

(1) The maximum frequency is limited by the I/O standard on the clock input pin. The 16-bit counter critical delay performs faster than this global clock input pin maximum frequency.

Table 5–25 shows the external I/O timing parameters for EPM1270 devices.

 Table 5–25.
 EPM1270 Global Clock External I/O Timing Parameters

				Γ	MAX II / N	IAX IIG			
			-3 Sp	eed Grade	–4 Spec	ed Grade	–5 Spee	ed Grade	
Symbol	Parameter	Condition	Min	Max	Min	Max	Min	Max	Unit
t _{PD1}	Worst case pin-to-pin delay through 1 look-up table (LUT)	10 pF	_	6.2	-	8.1	_	10.0	ns
t _{PD2}	Best case pin-to-pin delay through 1 LUT	10 pF		3.7	—	4.8		5.9	ns
t _{su}	Global clock setup time	_	1.2	_	1.5	—	1.9	—	ns
t _H	Global clock hold time	_	0	_	0	_	0	—	ns
t _{co}	Global clock to output delay	10 pF	2.0	4.6	2.0	5.9	2.0	7.3	ns
t _{cH}	Global clock high time	_	166		216	_	266	—	ps
t _{cL}	Global clock low time	_	166		216	_	266	_	ps
t _{cnt}	Minimum global clock period for 16-bit counter	_	3.3	_	4.0	_	5.0	_	ns
f _{cnt}	Maximum global clock frequency for 16-bit counter	—		304.0 (1)		247.5		201.1	MHz

Note to Table 5-25:

(1) The maximum frequency is limited by the I/O standard on the clock input pin. The 16-bit counter critical delay performs faster than this global clock input pin maximum frequency.

			MAX II / MAX IIG					MAX IIZ						
			–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		peed ade	–8 Speed Grade		
I/O Standa	rd	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
3.3-V LVTTL	16 mA	—	0	—	0	—	0	—	0	—	0	—	0	ps
	8 mA	—	65	—	84	—	104	_	-6	—	-2	—	-3	ps
3.3-V LVCMOS	8 mA	—	0	—	0	—	0	—	0	—	0	—	0	ps
	4 mA	—	65	—	84	—	104	—	-6	—	-2	—	-3	ps
2.5-V LVTTL /	14 mA	—	122		158	—	195	_	-63	—	-71	—	-88	ps
LVCMOS	7 mA	—	193		251	—	309	_	10	—	-1	—	1	ps
1.8-V LVTTL /	6 mA	—	568		738	—	909	_	128	—	118	—	118	ps
LVCMOS	3 mA	_	654	_	850	—	1,046	_	352	—	327	—	332	ps
1.5-V LVCMOS	4 mA	—	1,059	—	1,376	—	1,694	—	421	—	400	—	400	ps
	2 mA	—	1,167		1,517	—	1,867	_	757	—	743	—	743	ps
3.3-V PCI	20 mA	—	3	—	4	—	5	—	-6	—	-2	—	-3	ps

Table 5–29. External Timing Output Delay and $t_{\scriptscriptstyle OD}$ Adders for Fast Slew Rate

Ν			II XAN	/ MAX IIO)		MAX IIZ							
		–3 Speed Grade		–4 Speed Grade		–5 Speed Grade		–6 Speed Grade		–7 Speed Grade		–8 Speed Grade		
I/O Standa	rd	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Unit
3.3-V LVTTL	16 mA	_	7,064	—	6,745	—	6,426	—	5,966	—	5,992	—	6,118	ps
	8 mA		7,946		7,627		7,308		6,541		6,570	—	6,720	ps
3.3-V LVCMOS	8 mA	_	7,064		6,745		6,426		5,966		5,992	—	6,118	ps
	4 mA	_	7,946	_	7,627		7,308		6,541		6,570	—	6,720	ps
2.5-V LVTTL /	14 mA	_	10,434	_	10,115		9,796		9,141		9,154	—	9,297	ps
LVCMOS	7 mA	_	11,548	—	11,229		10,910		9,861		9,874	—	10,037	ps
1.8-V LVTTL /	6 mA	_	22,927	—	22,608		22,289		21,811		21,854	—	21,857	ps
LVCMOS	3 mA	_	24,731	_	24,412		24,093	_	23,081		23,034	—	23,107	ps
1.5-V LVCMOS	4 mA	_	38,723	—	38,404		38,085		39,121		39,124	—	39,124	ps
	2 mA	_	41,330	_	41,011		40,692		40,631		40,634	—	40,634	ps
3.3-V PCI	20 mA		261		339		418		6,644		6,627		6,914	ps

			MAX II / MAX II	G	MAX IIZ		
I/O Stand	lard	–3 Speed Grade	–4 Speed Grade	–5 Speed Grade	–6 Speed Grade	–7 Speed Grade	–8 Speed Grade
3.3-V LVTTL	304	304	304	304	304	304	MHz
3.3-V LVCMOS	304	304	304	304	304	304	MHz
2.5-V LVTTL	220	220	220	220	220	220	MHz
2.5-V LVCMOS	220	220	220	220	220	220	MHz
1.8-V LVTTL	200	200	200	200	200	200	MHz
1.8-V LVCMOS	200	200	200	200	200	200	MHz
1.5-V LVCMOS	150	150	150	150	150	150	MHz
3.3-V PCI	304	304	304	304	304	304	MHz

Table 5–33. MAX II Maximum Output Clock Rate fo	r I/0)
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JTAG Timing Specifications

Figure 5–6 shows the timing waveforms for the JTAG signals.



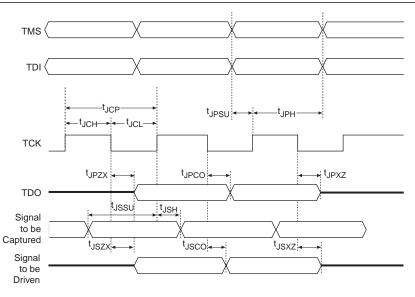


Table 5-34 shows the JTAG Timing parameters and values for MAX II devices.

Table 5-34. MAX II JTAG Timing Parameters (Part 1 of 2)

Symbol	Parameter	Min	Max	Unit
t _{JCP} (1)	TCK clock period for $V_{\text{CCIO1}} = 3.3 \text{ V}$	55.5		ns
	TCK clock period for $V_{\text{CCIO1}} = 2.5 \text{ V}$	62.5		ns
	TCK clock period for $V_{\text{CCIO1}} = 1.8 \text{ V}$	100	—	ns
	TCK clock period for $V_{\text{CCIO1}} = 1.5 \text{ V}$	143	—	ns
t _{jch}	TCK clock high time	20		ns
t _{JCL}	TCK clock low time	20	—	ns

Document Revision History

Table 5–35 shows the revision history for this chapter.

 Table 5–35.
 Document Revision History (Part 1 of 2)

Date and Revision	Changes Made	Summary of Changes
August 2009,	Added Table 5–28, Table 5–29, and Table 5–30.	Added information for
version 2.5	 Updated Table 5–2, Table 5–4, Table 5–14, Table 5–15, Table 5–16, Table 5–17, Table 5–18, Table 5–19, Table 5–20, Table 5–21, Table 5–22, Table 5–23, Table 5–24, Table 5–27, Table 5–31, Table 5–32, and Table 5–33. 	speed grade –8
November 2008,	Updated Table 5–2.	_
version 2.4	 Updated "Internal Timing Parameters" section. 	
October 2008,	Updated New Document Format.	_
version 2.3	 Updated Figure 5-1. 	
July 2008, version 2.2	 Updated Table 5–14 , Table 5–23 , and Table 5–24. 	_
March 2008, version 2.1	Added (Note 5) to Table 5–4.	_
December 2007,	 Updated (Note 3) and (4) to Table 5–1. 	Updated document with
version 2.0	 Updated Table 5–2 and added (Note 5). 	MAX IIZ information.
	 Updated ICCSTANDBY and ICCPOWERUP information and added IPULLUP information in Table 5–4. 	
	Added (Note 1) to Table 5–10.	
	 Updated Figure 5–2. 	
	Added (Note 1) to Table 5–13.	
	 Updated Table 5–13 through Table 5–24, and Table 5–27 through Table 5–30. 	
	 Added tCOMB information to Table 5–15. 	
	 Updated Figure 5–6. 	
	 Added "Referenced Documents" section. 	
December 2006,	Added note to Table 5–1.	—
version 1.8	 Added document revision history. 	
July 2006, version 1.7	 Minor content and table updates. 	_
February 2006,	 Updated "External Timing I/O Delay Adders" section. 	—
version 1.6	 Updated Table 5–29. 	
	 Updated Table 5–30. 	
November 2005, version 1.5	 Updated Tables 5-2, 5-4, and 5-12. 	—
August 2005,	 Updated Figure 5-1. 	_
version 1.4	Updated Tables 5-13, 5-16, and 5-26.	
	 Removed Note 1 from Table 5-12. 	



6. Reference and Ordering Information

MII51006-1.6

Software

MAX® II devices are supported by the Altera® Quartus® II design software with new, optional MAX+PLUS[®] II look and feel, which provides HDL and schematic design entry, compilation and logic synthesis, full simulation and advanced timing analysis, and device programming. Refer to the Design Software Selector Guide for more details about the Quartus II software features.

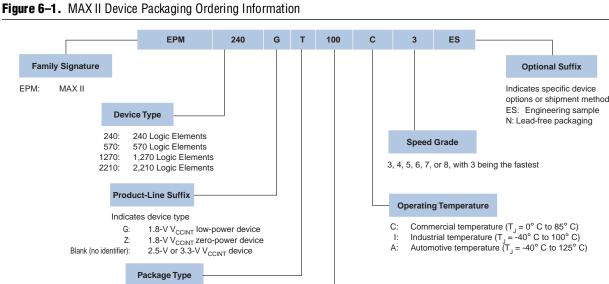
The Quartus II software supports the Windows XP/2000/NT, Sun Solaris, Linux Red Hat v8.0, and HP-UX operating systems. It also supports seamless integration with industry-leading EDA tools through the NativeLink interface.

Device Pin-Outs

Printed device pin-outs for MAX II devices are available on the Altera website (www.altera.com).

Ordering Information

Figure 6–1 describes the ordering codes for MAX II devices. For more information about a specific package, refer to the Package Information chapter in the MAX II Device Handbook.





T: Thin quad flat pack (TQFP)

F. FineLine BGA M: Micro FineLine BGA

Number of pins for a particular package

Pin Count